

ART UNIT: 2822

EXAMINER: Tonieae M. Thomas

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
ANDREW M. HAWRYLUK et al.)
Serial No.: 09/536,927)
Filed: March 27, 2000)
)

AMENDMENT DETAILS
OF AMENDMENT B

RECEIVED
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For: METHODS FOR ANNEALING A SUBSTRATE AND ARTICLE PRODUCED BY SUCH METHODS

In the Claims:

Amend claims 1 and 53 as follows:

1. (Amended) A method comprising the step of annealing at least one region of a semiconductor substrate **while minimizing the diffusion of dopant atoms during activation by using [with]** a pulsed beam of particles having a time duration less than or equal to 10^{-4} seconds.

53. (Amended) A method comprising the steps of annealing at least one integrated device formed in a semiconductor substrate **while minimizing the diffusion of dopant atoms during activation by using [with]** a pulsed beam of particles having a duration between 10^{-10} seconds and 10^{-4} seconds.